TOSHIBA Field Effect Transistor Silicon N Channel MOS Type (U-MOS IV)

# **TPCP8204**

Portable Equipment Applications Motor Drive Applications

- Small footprint due to small and thin package
- Low drain-source ON resistance:  $R_{DS}$  (ON) = 38 m $\Omega$  (typ.)

(VGS=10V)

- High forward transfer admittance: |Y<sub>fs</sub>| = 8 S (typ.)
  Low leakage current: IDSS = 10 µA (VDS = 30 V)
- Enhancement mode:  $V_{th} = 1.3$  to 2.5 V ( $V_{DS} = 10$  V,  $I_D = 1$ mA)

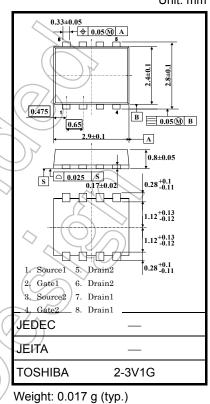
#### Absolute Maximum Ratings (Ta = 25°C)

Characteristics		Symbol	Rating	Unit
Drain-source voltage		V <sub>DSS</sub>	30	V
Drain-gate voltage ( $R_{GS} = 20 \text{ k}\Omega$ )		V <sub>DGR</sub>	30	V
Gate-source voltage		V <sub>GSS</sub>	±20	> v
Drain current	DC (Note 1)	I <sub>D</sub>	4.2	А
	Pulse (Note 1)	I <sub>DP</sub>	16.8	A
Drain power dissipation	Single-device operation (Note 3a)	P <sub>D (1)</sub>	1.48	
(t = 5 s) (Note 2a)	Single-device value at dual operation (Note 3b)	P <sub>D</sub> (2)	1.23	×
Drain power dissipation (t = 5 s) (Note 2b)	Single-device operation (Note 3a)	PD (1)	0.58	
	Single-device value at dual operation (Note 3b)	PD (2)	0.36	
Single pulse avalanche energy (Note 4)		EAS (	2.86	mJ
Avalanche current		IAR	2.1	А
Repetitive avalanche energy Single-device value at dual operation (Note 2a, 3b, 5)		E <sub>AR</sub>	0.009	mJ
Channel temperature		Tch	150	°C
Storage temperature range		T <sub>stg</sub>	-55~150	°C

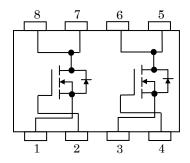
Note: For Notes 1 to 6, refer to the next page.

Using continuously under heavy loads (e.g. the application of high temperature/current/voltage and the significant change in temperature, etc.) may cause this product to decrease in the reliability significantly even if the operating conditions (i.e. operating temperature/current/voltage, etc.) are within the absolute maximum ratings. Please design the appropriate reliability upon reviewing the Toshiba Semiconductor Reliability Handbook ("Handling Precautions"/"Derating Concept and Methods") and individual reliability data (i.e. reliability test report and estimated failure rate, etc).

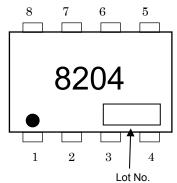
This transistor is an electrostatic-sensitive device. Handle with caution.



#### **Circuit Configuration**



#### Marking (Note 6)



Start of commercial production 2007-12

#### **Thermal Characteristics**

Characteristics		Symbol	Max	Unit	
Thermal resistance, channel to ambient	Single-device operation (Note 3a)	R <sub>th (ch-a) (1)</sub>	84.5	°C/W	
(t = 5 s) (Note 2a)	Single-device value at dual operation (Note 3b)	R <sub>th (ch-a) (2)</sub>	101.6		
Thermal resistance, channel to ambient	Single-device operation (Note 3a)	R <sub>th (ch-a)</sub> (1)	215.5	°C/W	
(t = 5 s) (Note 2b)	Single-device value at dual operation (Note 3b)	R <sub>th (ch-a) (2)</sub>	347.2		

Note 1: The channel temperature should not exceed 150°C during use.

Note 2: (a) Device mounted on a glass-epoxy board (a)



(b) Device mounted on a glass-epoxy board (b)

- Note 3: a) The power dissipation and thermal resistance values shown are for a single device. (During single-device operation, power is only applied to one device.)
  - b) The power dissipation and thermal resistance values shown are for a single device. (During dual operation, power is evenly applied to both devices.)
- Note 4:  $V_{DD} = 24 \text{ V}, \text{ T}_{ch} = 25^{\circ}\text{C}$  (initial),  $D = 0.5 \text{ mH}, \text{ R}_{G} = 25 \Omega$ ,  $I_{AR} = 2.1 \text{ A}$
- Note 5: Repetitive rating: pulse width limited by maximum channel temperature.
- Note 6: on the lower left of the marking indicates Pin 1.

\* Weekly code (3 digits):

Week of manufacture

- (01 for the first week of the year, continuing up to 52 or 53)

Year of manufacture

(The last digit of the calendar year)

### Electrical Characteristics (Ta = 25°C)

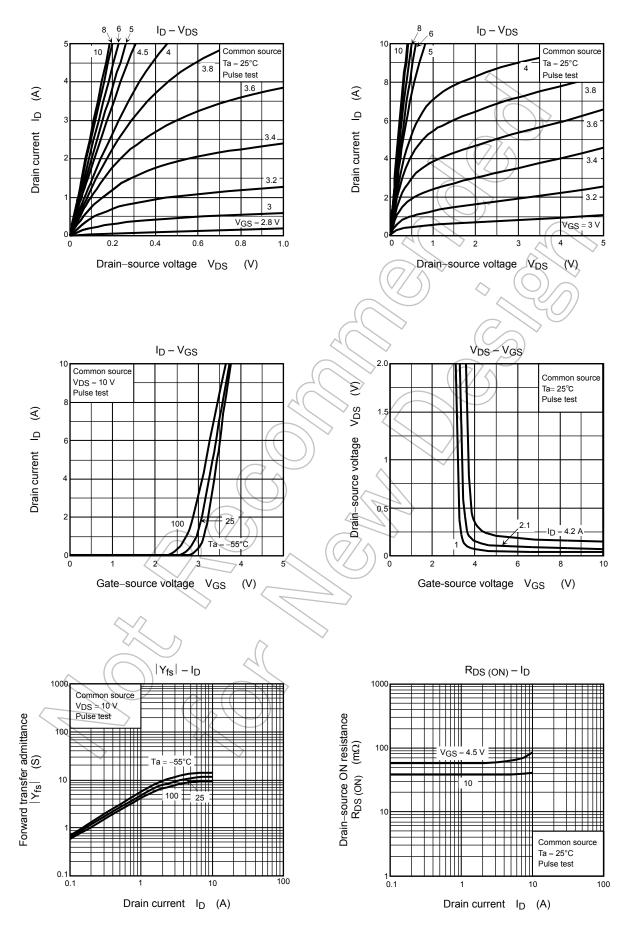
Characteristics		Symbol	Test Condition	Min	Тур.	Max	Unit
Gate leakage current		I <sub>GSS</sub>	$V_{GS} = \pm 20 \text{ V}, V_{DS} = 0 \text{ V}$		_	±100	nA
Drain cut-off current		I <sub>DSS</sub>	$V_{DS} = 30 \text{ V}, \text{ V}_{GS} = 0 \text{ V}$	>	_	10	μA
Drain-source breakdown voltage		V (BR) DSS	$I_D = 10 \text{ mA}, V_{GS} = 0 \text{ V}$	30		_	V
		V (BR) DSX	$I_D = 10 \text{ mA}, V_{GS} = -20 \text{ V}$	10	2_		v
Gate threshold voltage		V <sub>th</sub>	$V_{DS} = 10 \text{ V}, \text{ I}_{D} = 1 \text{ mA}$	1.3		2.5	V
Drain-source ON resistance		R <sub>DS (ON)</sub>	V <sub>GS</sub> = 4.5 V, I <sub>D</sub> = 2.1 A	2	58	77	mΩ
			$V_{GS} = 10 \text{ V}, \text{ I}_{D} = 2.1 \text{ A}$	>	38	50	
Forward transfer admittance		Y <sub>fs</sub>	$V_{DS} = 10 \text{ V}, \text{ I}_{D} = 2.1 \text{ A}$	4	8		S
Input capacitance		C <sub>iss</sub>	$\langle \langle \rangle$	_	190	$\rightarrow$	
Reverse transfer capacitance		C <sub>rss</sub>	V <sub>DS</sub> = 10 V, V <sub>GS</sub> = 0 V, f = 1 MHz		45	_	pF
Output capacitance		C <sub>oss</sub>	$(\checkmark)$	((	65	_	
Switching time	Rise time	tr	$V_{GS} = 2.1 \text{ A}$		4.5	_	
	Turn-on time	t <sub>on</sub>		D	9.0		
	Fall time	tf	v v v v v v v v v v v v v v v v v v v	)_	3.0	_	ns
	Turn-off time	toff	Duty $\leq$ 1%, t <sub>w</sub> = 10 µs		12.0		
Total gate charge (gate-source plus gate-drain)		$\sim$	—	4.6	_	_	
Gate-source charge 1 Qgs1		Qgs1	$V_{DD} \approx 24$ V, $V_{GS} = 10$ V, $I_D = 4.2$ A	—	0.7	—	nC
Gate-drain ("miller") charge		Q <sub>gd</sub>		—	1.4	_	

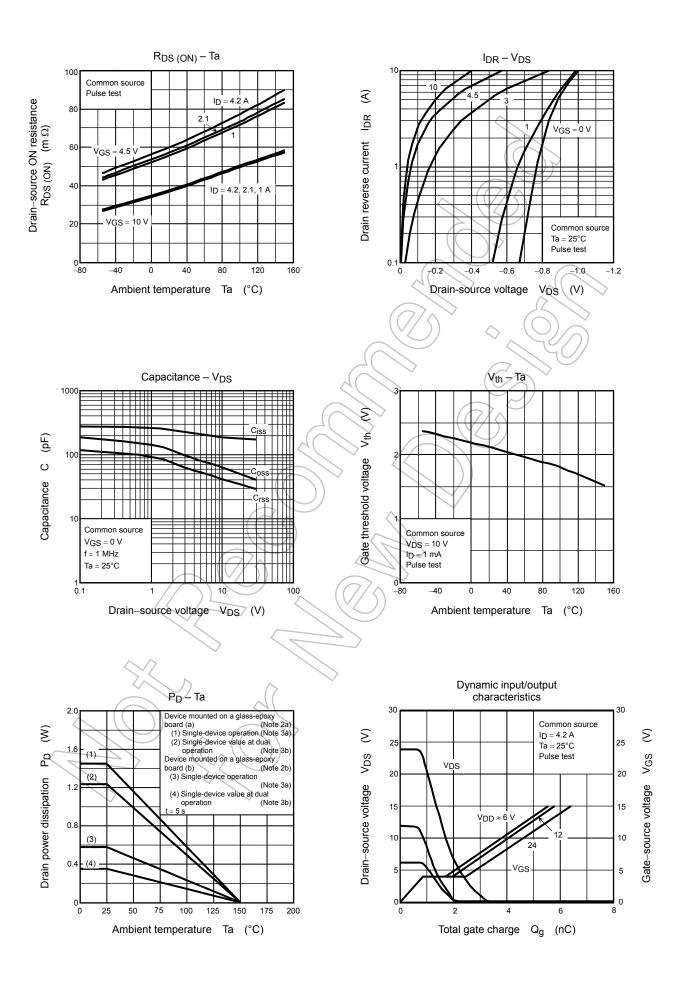
# Source-Drain Ratings and Characteristics (Ta = 25°C)

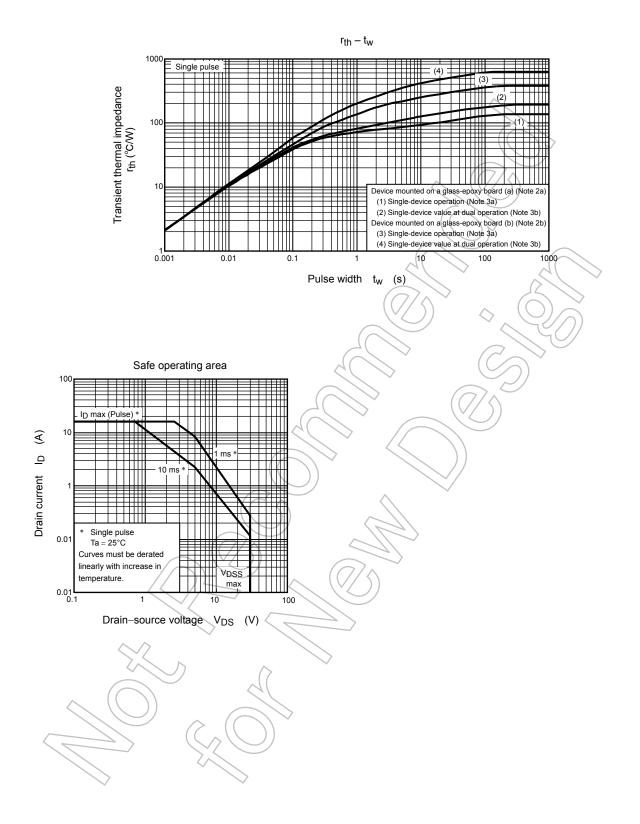
Characteristics	Symbol Test Condition	Min	Тур.	Max	Unit
Drain reverse current Pulse (Note 1)	I <sub>DRP</sub> —	_	_	16.8	А
Forward voltage (diode)	$V_{DSF}$ $I_{DR} = 4.2 \text{ A}, V_{GS} = 0 \text{ V}$	—		-1.2	V



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